

Appl. No. 10/782,187
Amdt. dated October 26, 2005
Reply to Office action of July 27, 2005

Amendments to the Specification:

Please amend the specification as follows:

Please replace paragraph [0019] with the following amended paragraph:

[0019] Fig. 13 is a flow chart showing a process for measuring characteristics of a film in accordance with the present invention~~[[.]]~~; and

Please add the following paragraph after paragraph [0019] on page 3 of the specification.

[0020] Fig. 14 is a side view of the imprinting layer shown in Fig. 5, having a defect therein.

Please replace paragraph [0039] with the following amended paragraph:

[0039] The embodiments of the present invention described above are exemplary. Although the invention has been described with respect to measuring film thickness anomalies, other anomalies may be determined. For example, distortions 99 in the pattern may formed in imprinting layer 40, shown as a loss of planarity in sub-portion 52 in Fig. 14, may be sensed and the cause of the same determined employing the present invention. As a result, the system may be employed to detect anomalies in critical dimension variations of the pattern features, as well as, errors in field-to-field and/or layer-to-layer alignment. With such information adaptive control may be employed to

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correct/compensate for such anomalies. These measurements may be made either *in-situ* or post processes. Furthermore, the invention has been discussed with respect to being placed upon an imprint lithography machine. However, the invention may be performed by a separate machine and apart from the imprint lithography process.

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